

# INK0410AP2

High Speed Switching  
Silicon N-channel MOSFET

## DESCRIPTION

INK0410AP2 is a Silicon N-channel MOSFET.

This product is most suitable for use such as portable machinery, because of low voltage drive and low on resistance.

## FEATURE

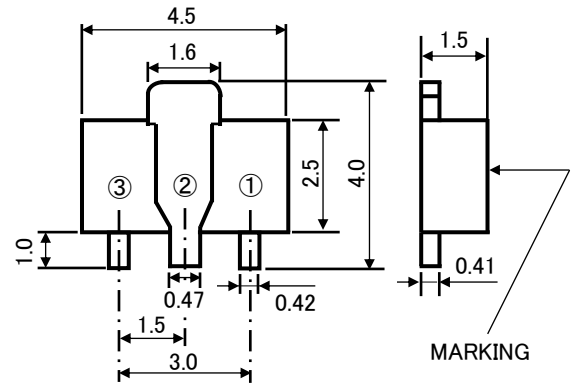
- Input impedance is high, and not necessary to consider a drive electric current.
- High drain current  $I_D=3.8A$
- Drive voltage 4.0V
- Low on Resistance.  
 $R_{DS(ON)}=52m\Omega$  (TYP) (@ $V_{GS}=10V$ )  
 $R_{DS(ON)}=58m\Omega$  (TYP) (@ $V_{GS}=4.5V$ )

## APPLICATION

High-speed switching, analog switching, etc.

## OUTLINE DRAWING

UNIT:mm



TERMINAL CONNECTOR

JEITA: SC-62

①: GATE

JEDEC: SOT-89

②: DRAIN

③: SOURCE

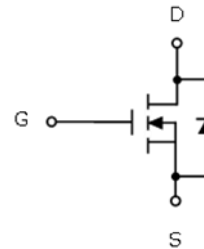
## MAXIMUM RATINGS ( $T_a=25^\circ C$ )

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DS}$	60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current(DC) ※1	$I_D$	3.8	A
Drain Current(Pulse) ※2	$I_{DP}$	13	A
Total Power Dissipation ※1	$P_D$	1.5	W
Junction Temperature	$T_j$	+150	$^\circ C$
Storage Temperature	$T_{stg}$	-55~+150	$^\circ C$

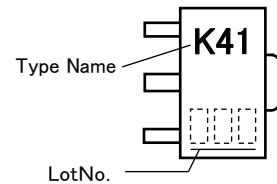
※1: Package mounted on glass-epoxy substrate  
(20mm×20mm×1.0mm, Cu pad 256mm<sup>2</sup>).

※2:  $P_w \leq 1ms$ , Duty cycle  $\leq 1\%$

## EQUIVALENT CIRCUIT



## MARKING



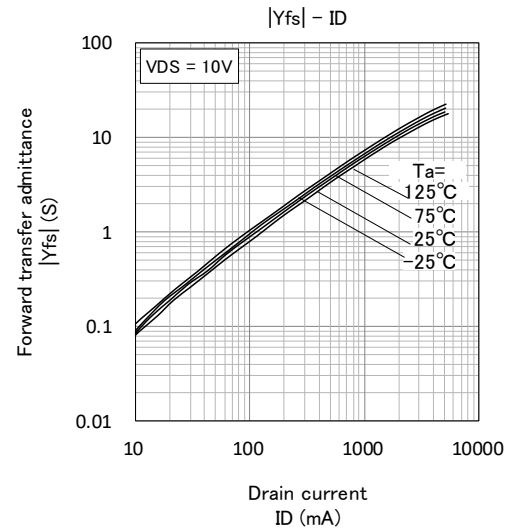
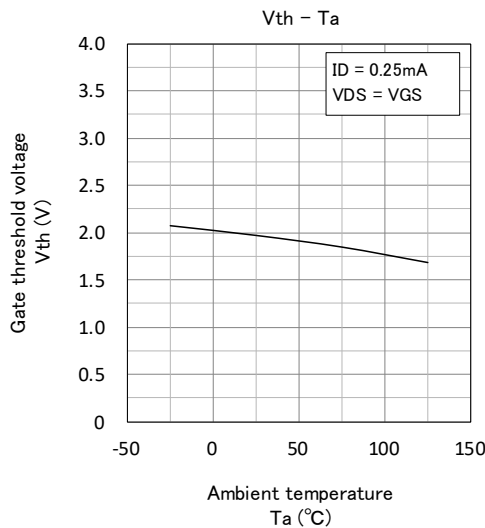
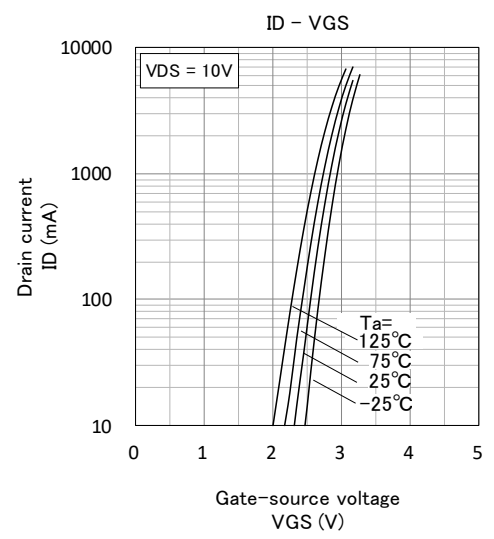
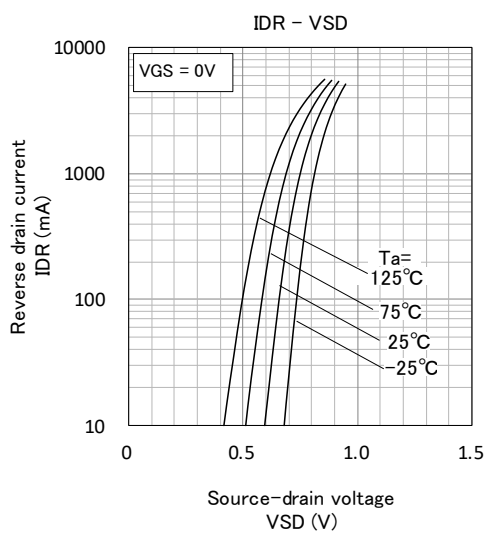
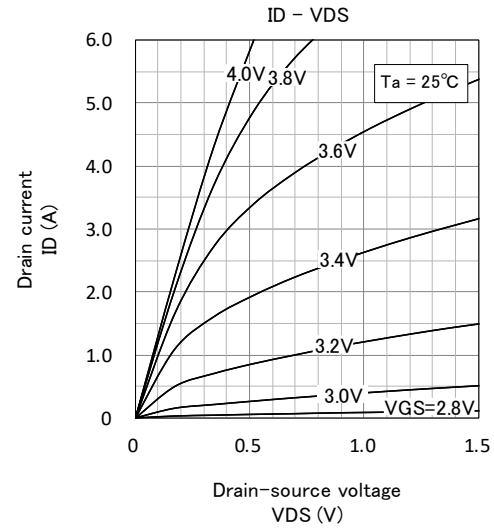
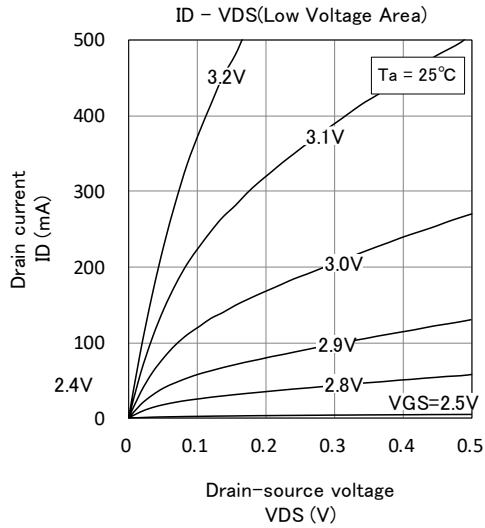
## ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ C$ )

Parameter	Symbol	Test Condition	Limit			Unit
			MIN	TYP	MAX	
Drain-Source Breakdown Voltage	$V(BR)_{DSS}$	$I_D=250\mu A, V_{GS}=0V$	60	-	-	V
Gate-Source Leak Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 1.0$	$\mu A$
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=60V, V_{GS}=0V$	-	-	1.0	$\mu A$
Gate Threshold Voltage	$V_{th}$	$I_D=250\mu A, V_{DS}=10V$	1.0	-	2.5	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$I_D=3.8A, V_{GS}=4.5V$	-	58	80	m $\Omega$
		$I_D=3.8A, V_{GS}=10V$	-	52	70	
Input Capacitance	$C_{iss}$	$V_{DS}=10V, V_{GS}=0V, f=1MHz$	-	580	-	pF
Output Capacitance	$C_{oss}$		-	60	-	
Reverse Transfer Capacitance	$C_{rss}$		-	40	-	
Switching Time	$t_{on}$	$V_{DD}=20V, I_D=200mA, V_{GS}=5V$	-	30	-	ns
	$t_{off}$		-	40	-	

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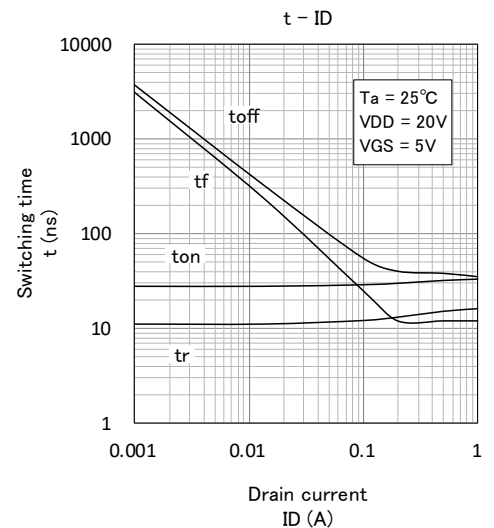
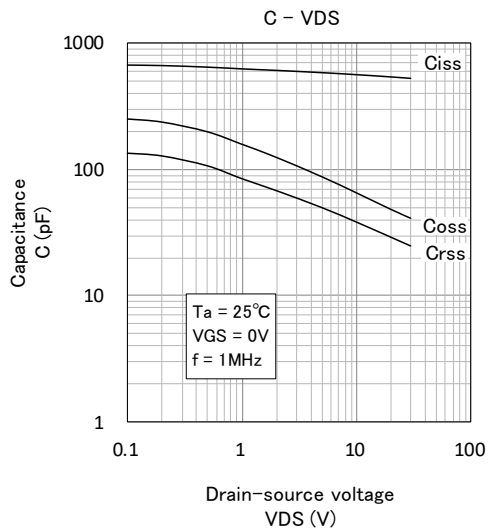
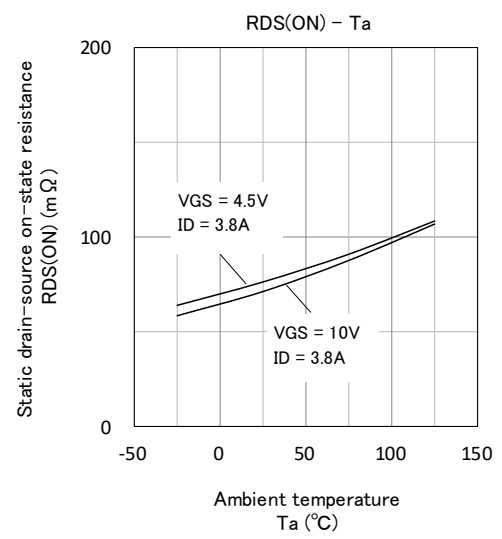
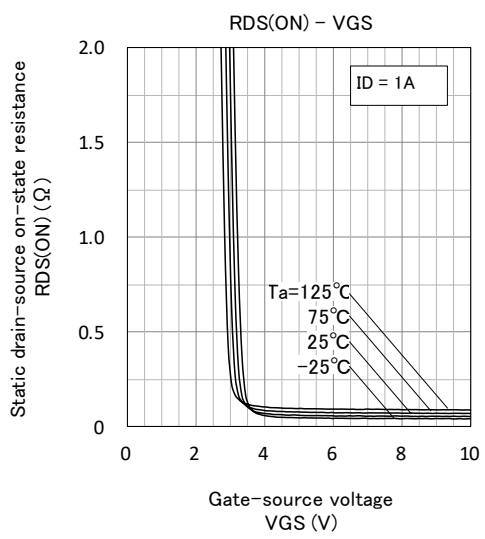
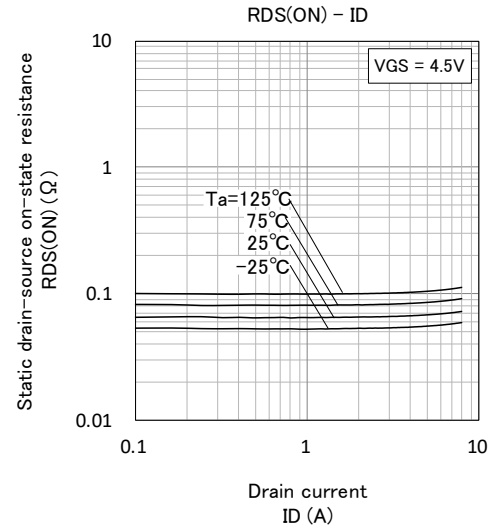
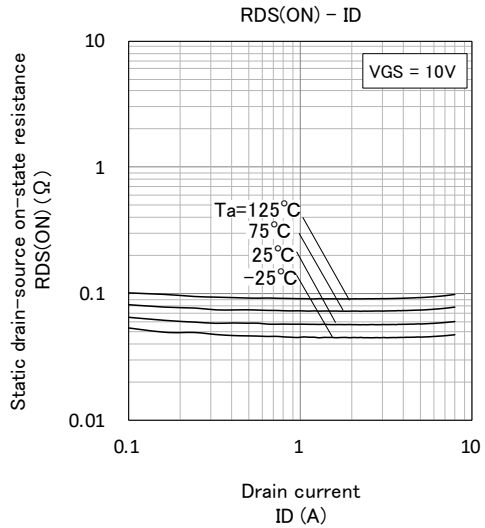
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## TYPICAL CHARACTERISTICS



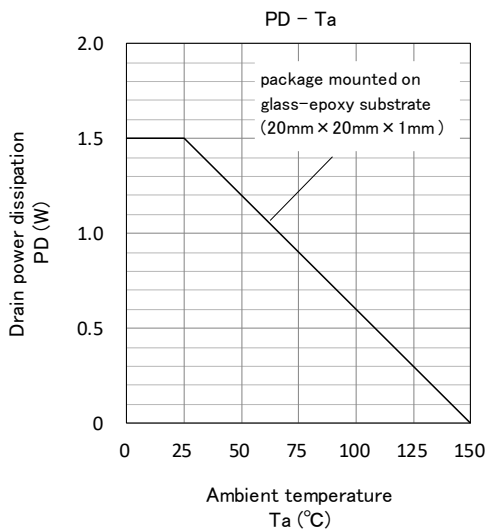
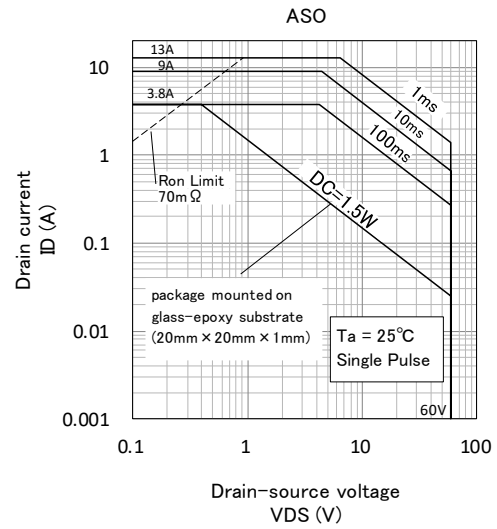
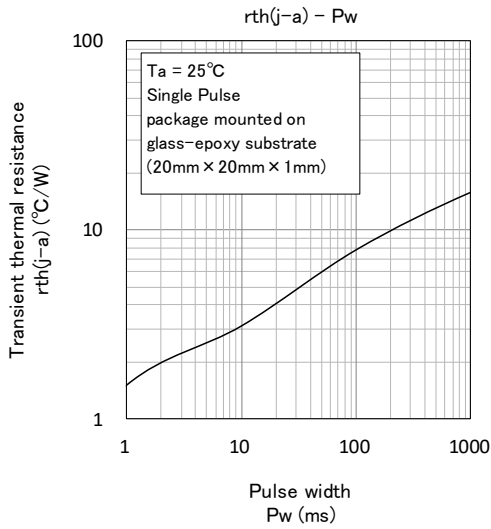
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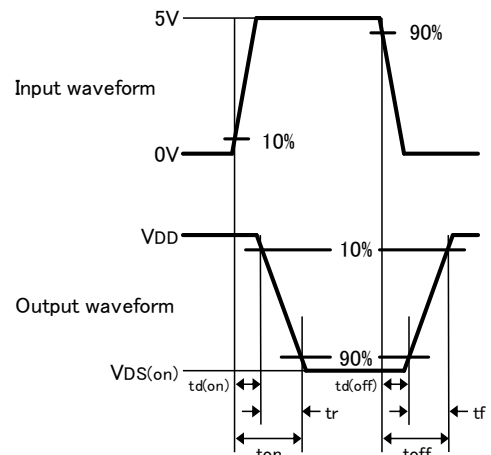
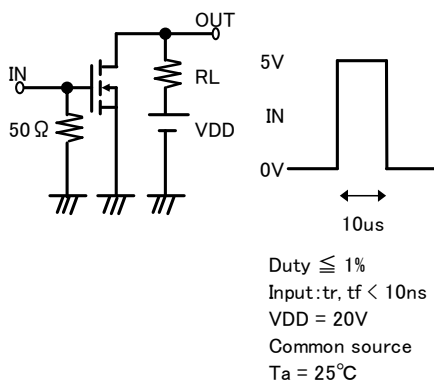


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### Switching time test condition



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